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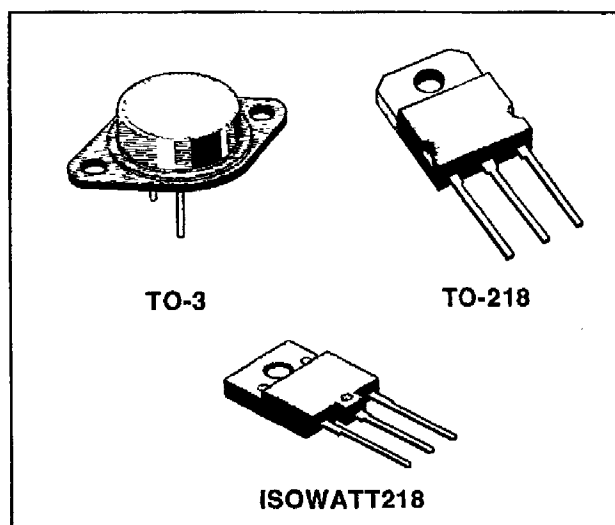
BUW42/42P/42PFI BUW42A/42AP/42APFI

HIGH VOLTAGE POWER SWITCH

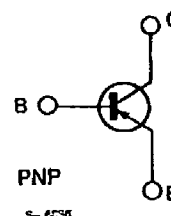
DESCRIPTION

The BUW42/A, BUW42P/42AP and BUW42PFI/APFI are silicon multi-epitaxial mesa PNP transistors mounted respectively in TO-3 metal case, TO-218 plastic package and ISOWATT218 fully isolated package.

They are intended in fast switching applications for high output power.



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	BUW			Unit
		42/P/PFI	42A/AP/APFI		
V_{CES}	Collector-emitter Voltage ($V_{BE} = 0$)	- 400	- 450		V
V_{CEO}	Collector-emitter Voltage ($I_B = 0$)	- 350	- 400		V
V_{EBO}	Emitter-base Voltage ($I_C = 0$)	- 7			V
I_C	Collector Current	- 15			A
I_{CM}	Collector Peak Current	- 30			A
I_B	Base Current	- 10			A
		TO-3	TO-218	ISOWATT218	
P_{tot}	Total Dissipation at $T_c < 25^\circ\text{C}$	150	105	65	W
T_{stg}	Storage Temperature	- 65 to 175	- 65 to 150	- 65 to 150	$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	175	150	150	$^\circ\text{C}$

Quality Semi-Conductors

THERMAL DATA

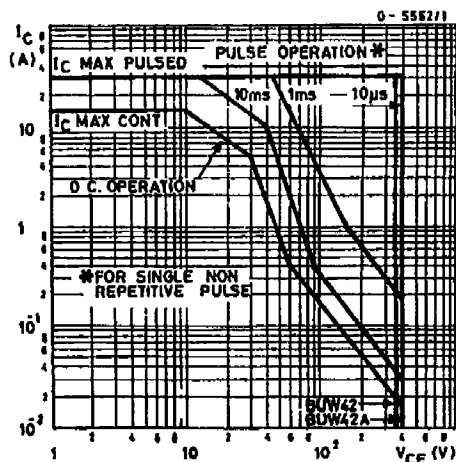
		TO-3	SOT-93	ISOWATT218	Unit	
R _{th J-case}	Thermal Resistance Junction-case	Max	1.2	1.2	1.92	°C/W

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector Cutoff Current ($V_{BE} = 0$)	$V_{CE} = -400\text{V}$ for BUW42/P/PFI $V_{CE} = -450\text{V}$ for BUW42A/AP/APFI			-1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}$ for BUW42/P/PFI $V_{EB} = -7\text{V}$ for BUW42A/AP/APFI			-1	mA
$V_{CE(sus)}^*$	Collector-emitter Sustaining Voltage ($I_B = 0$)	$I_C = -100\text{mA}$ for BUW42/P/PFI for BUW42A/AP/APFI	-350 -400			V V
$V_{CE(sat)}^*$	Collector-emitter Saturation Voltage	$I_C = -10\text{A}$ $I_B = -3\text{A}$			-1.5	V
$V_{BE(sat)}^*$	Base-emitter Saturation Voltage	$I_C = -10\text{A}$ $I_B = -3\text{A}$			-2	V
h_{FE}^*	DC Current Gain	$I_C = -3\text{A}$ $V_{CE} = -5\text{V}$	12		80	
t_{on} t_s t_f	RESISTIVE LOAD Turn-on Time Storage Time Fall Time	$V_{CC} = -250\text{V}$ $I_C = -10\text{A}$ $I_{B1} = -I_{B2} = -3.3\text{A}$		0.3 0.5 0.3	0.6 1.5 0.6	μs μs μs

* Pulsed : pulse duration = 300 μs , duty cycle = 1.5 %.

Safe Operating Areas.
(TO-3).



Safe Operating Areas.
(TO-218, ISOWATT218).

